

# Ullrich Pfeiffer

## List of Publications by Year in descending order

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209  
papers

6,437  
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147566

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#	ARTICLE	IF	CITATIONS
1	A SiGe HBT 215–240 GHz DCA IQ TX/RX Chipset With Built-In Test of USB/LSB RF Asymmetry for 100+ Gb/s Data Rates. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 1696-1714.	2.9	15
2	An Ultra Low Current Measurement Mixed-Signal ASIC for Radiation Monitoring Using Ionisation Chambers. IEEE Sensors Journal, 2022, 22, 2142-2150.	2.4	4
3	Broadband Modeling, Analysis, and Characterization of SiGe HBT Terahertz Direct Detectors. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 1314-1333.	2.9	12
4	A Broadband 300 GHz Power Amplifier in a 130 nm SiGe BiCMOS Technology for Communication Applications. IEEE Journal of Solid-State Circuits, 2022, 57, 2024-2034.	3.5	15
5	Towards the next generation of CERN radiation monitoring front end ASICs. Journal of Instrumentation, 2022, 17, C04029.	0.5	0
6	InP-Based THz Beam Steering Leaky-Wave Antenna. IEEE Transactions on Terahertz Science and Technology, 2021, 11, 218-230.	2.0	38
7	Comparative Analysis of Ultra-Low Current Measurement Topologies With Implementation in 130 nm Technology. IEEE Access, 2021, 9, 63855-63864.	2.6	5
8	Performance Limits of THz Dispersive Spectroscopes Employing Super-Resolution Imaging. IEEE Transactions on Terahertz Science and Technology, 2021, , 1-1.	2.0	1
9	34.3 A 32–32 Pixel 0.46-to-0.75THz Light-Field Camera SoC in 0.13µm CMOS. , 2021, , .		10
10	Terahertz refractive index-based morphological dilation for breast carcinoma delineation. Scientific Reports, 2021, 11, 6457.	1.6	18
11	Resolution Limits of Hyper-Hemispherical Silicon Lens-Integrated THz Cameras Employing Geometrical Multiframe Super-Resolution Imaging. IEEE Transactions on Terahertz Science and Technology, 2021, 11, 277-286.	2.0	5
12	Terahertz Rectennas on Flexible Substrates Based on One-Dimensional Metal–Insulator–Graphene Diodes. ACS Applied Electronic Materials, 2021, 3, 3747-3753.	2.0	11
13	Broadband Lens-Integrated CMOS Camera-Type THz Compact Antenna Test Range. IEEE Transactions on Terahertz Science and Technology, 2021, 11, 527-537.	2.0	4
14	Radial Distortion in Silicon Lens-Integrated THz Cameras. , 2021, , .		1
15	Silicon Lens Optimization to Create Diffuse, Uniform Illumination from Incoherent THz Source Arrays. Journal of Infrared, Millimeter, and Terahertz Waves, 2021, 42, 947-959.	1.2	2
16	A 239–298 GHz Power Amplifier in an Advanced 130 nm SiGe BiCMOS Technology for Communications Applications. , 2021, , .		7
17	THz transmission experiments – A data rate of 80 Gbps was demonstrated using Kasami codes. , 2021, , .		0
18	Amorphous Indium-Gallium-Zinc-Oxide TFTs Patterned by Self-Aligned Photolithography Overcoming the GHz Threshold. IEEE Electron Device Letters, 2020, 41, 1786-1789.	2.2	14

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19	Novel 3-D Multilayer Terahertz Packaging Technology for Integrating Photodiodes Arrays and Rectangular Waveguide-Power Combiners. IEEE Transactions on Microwave Theory and Techniques, 2020, 68, 4611-4619.	2.9	9
20	CMOS THz Camera Used as Compact Antenna Test Range. , 2020, , .		5
21	A 64-Pixel 0.42-THz Source SoC With Spatial Modulation Diversity for Computational Imaging. IEEE Journal of Solid-State Circuits, 2020, 55, 3281-3293.	3.5	27
22	Signal-processing Challenges in Leveraging 100 Gb/s Wireless THz. , 2020, , .		14
23	Toward Mobile Integrated Electronic Systems at THz Frequencies. Journal of Infrared, Millimeter, and Terahertz Waves, 2020, 41, 846-869.	1.2	32
24	A QPSK 110-Gb/s Polarization-Diversity MIMO Wireless Link With a 220-255 GHz Tunable LO in a SiGe HBT Technology. IEEE Transactions on Microwave Theory and Techniques, 2020, 68, 3834-3851.	2.9	56
25	Terahertz Spectroscope Using CMOS Camera and Dispersive Optics. IEEE Transactions on Terahertz Science and Technology, 2020, 10, 513-523.	2.0	15
26	29.1 A 0.42THz 9.2dBm 64-Pixel Source-Array SoC with Spatial Modulation Diversity for Computational Terahertz Imaging. , 2020, , .		14
27	A 210-291-GHz (8- $\mu$ m) Frequency Multiplier Chain With Low Power Consumption in 0.13- $\mu$ m SiGe. IEEE Microwave and Wireless Components Letters, 2020, 30, 512-515.	2.0	10
28	CMOS Camera-Type THz Compact Antenna Test Range for Far-Field Radiation Pattern Analysis. , 2020, , .		2
29	Silicon-integrated Single Pixel Terahertz Camera. , 2020, , .		0
30	Broadband Spectro-Spatial Characterization of CW Terahertz Photoemitter Using CMOS Camera. , 2020, , .		1
31	Ex Vivo Breast Tumor Identification: Advances Toward a Silicon-Based Terahertz Near-Field Imaging Sensor. IEEE Microwave Magazine, 2019, 20, 32-46.	0.7	18
32	Optimization and Performance Limits of a 64-QAM Wireless Communication Link at 220-260 GHz in a SiGe HBT Technology. , 2019, , .		13
33	A Broadband Dual-Polarized Terahertz Direct Detector in a 0.13- $\mu$ m SiGe HBT Technology. , 2019, , .		18
34	Resolution Limits in Lens-Integrated CMOS THz Cameras Employing Super-Resolution Imaging. , 2019, , .		7
35	Performance Characterization Method of Broadband Terahertz Video Cameras. , 2019, , .		11
36	A Lens-Coupled On-Chip Antenna for Dual-Polarization SiGe HBT THz Direct Detector. IEEE Antennas and Wireless Propagation Letters, 2019, 18, 2404-2408.	2.4	29

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37	Evaluation of the Beyond- $\text{60 GHz}$ Operation of an ICZO TFT-Based RF Self-Mixing Circuit. IEEE Microwave and Wireless Components Letters, 2019, 29, 119-121.	2.0	5
38	A 16-QAM 100-Gb/s 1-M Wireless Link With an EVM of 17% at 230 GHz in an SiGe Technology. IEEE Microwave and Wireless Components Letters, 2019, 29, 297-299.	2.0	134
39	Effects of proton irradiation on 60 GHz CMOS transceiver chip for multi-Gbps communication in high-energy physics experiments. Journal of Engineering, 2019, 2019, 5391-5396.	0.6	2
40	RF Front-End Impairments for Ultra-Broadband Wireless Communication above 200 GHz. , 2019, , .		2
41	The Influence of RF Front-End Imperfections on Performance of a 220-260 GHz Tunable M-QAM Wireless Link in SiGe HBT Technology. , 2019, , .		0
42	Incoherent Power Combining of THz Source Arrays. , 2019, , .		5
43	A Broadband Antenna-Coupled Terahertz Direct Detector in a 0.13- $\mu\text{m}$ SiGe HBT Technology. , 2019, , .		10
44	Terahertz Imaging and Sensing Applications With Silicon-Based Technologies. IEEE Transactions on Terahertz Science and Technology, 2019, 9, 1-19.	2.0	249
45	A 65 Gbps QPSK one meter wireless link operating at a 225-255 GHz tunable carrier in a SiGe HBT technology. , 2018, , .		41
46	NearSense – Advances Towards a Silicon-Based Terahertz Near-Field Imaging Sensor for Ex Vivo Breast Tumour Identification. Frequenz, 2018, 72, 93-99.	0.6	4
47	Diffuse Beam with Electronic THz Source Array. , 2018, , .		6
48	Incoherent, spatially-mapped THz spectral analysis. , 2018, , .		9
49	Performance Evaluation of a 32-QAM 1-Meter Wireless Link Operating at 220-260 GHz with a Data-Rate of 90 Cbps. , 2018, , .		20
50	A Solid-State 0.56 THz Near-Field Array for $\mu\text{m}$ -Scale Surface Imaging. , 2018, , .		3
51	A High-Speed QPSK/16-QAM 1-m Wireless Link with a Tunable 220-260 GHz LO Carrier in SiGe HBT Technology. , 2018, , .		3
52	Studies on PCA for Breast Tissue Segmentation. , 2018, , .		0
53	Object Feature Extraction with Focused Terahertz Plenoptic Imaging. , 2018, , .		3
54	A 128-Pixel System-on-a-Chip for Real-Time Super-Resolution Terahertz Near-Field Imaging. IEEE Journal of Solid-State Circuits, 2018, 53, 3599-3612.	3.5	28

#	ARTICLE	IF	CITATIONS
55	Towards 100 Gbps: A Fully Electronic 90 Gbps One Meter Wireless Link at 230 GHz. , 2018, , .		11
56	Performance Evaluation of a 220â€“260 GHz LO Tunable BPSK/QPSK Wireless Link in SiGe HBT Technology. , 2018, , .		3
57	A Terahertz Direct Detector in 22nm FD-SOI CMOS. , 2018, , .		18
58	Current Status of Terahertz Integrated Circuits - From Components to Systems. , 2018, , .		16
59	100 Gbps and beyond: Hardware in the Loop experiments with PSSS modulation using 230 GHz RF frontend. , 2018, , .		10
60	Towards 100 Gbps: A Fully Electronic 90 Gbps One Meter Wireless Link at 230 GHz. , 2018, , .		5
61	Pilot study of freshly excised breast tissue response in the 300 â€“ 600 GHz range. Biomedical Optics Express, 2018, 9, 2930.	1.5	48
62	A 128-pixel 0.56THz sensing array for real-time near-field imaging in 0.13Î¼m SiGe BiCMOS. , 2018, , .		10
63	A 219â€“266 GHz LO-tunable direct-conversion IQ receiver module in a SiGe HBT technology. International Journal of Microwave and Wireless Technologies, 2018, 10, 587-595.	1.5	12
64	Active Multiple Feed On-Chip Antennas With Efficient In-Antenna Power Combining Operating at 200â€“320 GHz. IEEE Transactions on Antennas and Propagation, 2017, 65, 416-423.	3.1	33
65	30 Gbps wireless data transmission with fully integrated 240 GHz silicon based transmitter. , 2017, , .		7
66	High data-rate communication link at 240 GHz with on-chip antenna-integrated transmitter and receiver modules in SiGe HBT technology. , 2017, , .		12
67	Solid-State Terahertz Superresolution Imaging Device in 130-nm SiGe BiCMOS Technology. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 4357-4372.	2.9	38
68	Low-Cost 0.5 THz computed tomography based on silicon components. , 2017, , .		12
69	Towards THz high data-rate communication. , 2017, , .		3
70	Real100G.RF: A Fully Packaged 240 GHz Transmitter with In-Antenna Power Combining in 0.13 Î¼m SiGe Technology. Frequenz, 2017, 71, 415-425.	0.6	0
71	THz spectroscopy and imaging for breast cancer detection in the 300â€“500 GHz range. , 2017, , .		5
72	Investigations on the plenoptics based image generation for THz reflection imaging. , 2017, , .		4

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73	A lens-integrated 430 GHz SiGe HBT source with up to $\sim 6.3$ dBm radiated power. , 2017, , .		30
74	A novel approach of aqueous solution analysis using a fully-integrated terahertz near-field sensor. , 2017, , .		0
75	Program FFlexCom â€” High frequency flexible bendable electronics for wireless communication systems. , 2017, , .		12
76	A 240 GHz high-speed transmission link with highly-integrated transmitter and receiver modules in SiGe HBT technology. , 2017, , .		12
77	A 219â€“266 GHz fully-integrated direct-conversion IQ receiver module in a SiGe HBT technology. , 2017, , .		18
78	Wireless data transmission for high energy physics applications. EPJ Web of Conferences, 2017, 150, 00002. , 2017, , .	0.1	1
79	The EU DOTSEVEN Project: Overview and Results. , 2016, , .		17
80	A wideband fully integrated SiGe chipset for high data rate communication at 240 GHz. , 2016, , .		34
81	A 275 GHz amplifier in 0.35 $\mu\text{m}$ SiGe. , 2016, , .		2
82	Towards passive imaging with CMOS THz cameras. , 2016, , .		12
83	3-D high-resolution imaging at 240 GHz with a single-chip FMCW monostatic radar in SiGe HBT technology. , 2016, , .		3
84	A fully-integrated terahertz near-field sensor for super-resolution imaging in SiGe BiCMOS. , 2016, , .		4
85	Zero gate-bias terahertz detection with an asymmetric NMOS transistor. , 2016, , .		8
86	25.1 A fully integrated 0.55THz near-field sensor with a lateral resolution down to 8 $\mu\text{m}$ in 0.13 $\mu\text{m}$ SiGe BiCMOS. , 2016, , .		5
87	A 210â€“270-GHz Circularly Polarized FMCW Radar With a Single-Lens-Coupled SiGe HBT Chip. IEEE Transactions on Terahertz Science and Technology, 2016, 6, 771-783. , 2016, , .	2.0	104
88	A 0.55 THz Near-Field Sensor With a $\mu\text{m}$ -Range Lateral Resolution Fully Integrated in 130 nm SiGe BiCMOS. IEEE Journal of Solid-State Circuits, 2016, 51, 3063-3077. , 2016, , .	3.5	22
89	A 200â€“225 GHz SiGe Power Amplifier with peak $P_{\text{sat}}$ of 9.6 dBm using wideband power combination. , 2016, , .		13
90	Terahertz Light-Field Imaging. IEEE Transactions on Terahertz Science and Technology, 2016, , 1-9. , 2016, , .	2.0	24

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91	An OOK-modulator at 240 GHz with 20 GHz bandwidth. , 2016, , .		5
92	A Fully Integrated 240-GHz Direct-Conversion Quadrature Transmitter and Receiver Chipset in SiGe Technology. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 562-574.	2.9	129
93	A 240-GHz circularly polarized FMCW radar based on a SiGe transceiver with a lens-coupled on-chip antenna. International Journal of Microwave and Wireless Technologies, 2015, 7, 415-423.	1.5	11
94	J-band amplifier design using gain-enhanced cascodes in 0.13 $\mu\text{m}$ SiGe. International Journal of Microwave and Wireless Technologies, 2015, 7, 339-347.	1.5	6
95	A broadband 240 GHz lens-integrated polarization-diversity on-chip circular slot antenna for a power source module in SiGe technology. , 2015, , .		8
96	A 246 GHz fundamental source with a peak output power of 2.8 dBm. , 2015, , .		5
97	Compact Model Validation Strategies Based on Dedicated and Benchmark Circuit Blocks for the mm-Wave Frequency Range. , 2015, , .		9
98	A lens-coupled 210â€“270 GHz circularly polarized FMCW radar transceiver module in SiGe technology. , 2015, , .		16
99	Antenna-Coupled MOSFET Bolometers for Uncooled THz Sensing. IEEE Transactions on Terahertz Science and Technology, 2015, 5, 902-913.	2.0	22
100	A lens-integrated on-chip circular slot antenna for a 240 GHz power source in SiGe technology. , 2015, , .		4
101	A wideband 240 GHz lens-integrated circularly polarized on-chip annular slot antenna for a FMCW radar transceiver module in SiGe technology. , 2015, , .		26
102	An antenna-coupled 0.49 THz SiGe HBT source for active illumination in terahertz imaging applications. , 2015, , .		14
103	Efficiency Enhancement for THz Power Amplifier. , 2015, , 135-154.		0
104	160-GHz to 1-THz Multi-Color Active Imaging With a Lens-Coupled SiGe HBT Chip-Set. IEEE Transactions on Microwave Theory and Techniques, 2015, 63, 520-532.	2.9	87
105	THz Direct Detector and Heterodyne Receiver Arrays in Silicon Nanoscale Technologies. Journal of Infrared, Millimeter, and Terahertz Waves, 2015, 36, 998-1032.	1.2	39
106	Numerical Computation of Temperature Elevation in Human Skin Due to Electromagnetic Exposure in the THz Frequency Range. IEEE Transactions on Terahertz Science and Technology, 2015, 5, 978-989.	2.0	8
107	Silicon-based Sources and Detectors for Terahertz Applications. , 2014, , .		0
108	Development and application of electromagnetic field excitation models for dosimetry studies in the THz range. , 2014, , .		2

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109	SiGe Transmitter and Receiver Circuits for Emerging Terahertz Applications. , 2014, , .		1
110	A 233-GHz low noise amplifier with 22.5dB gain in 0.13&#x03BC;m SiGe. , 2014, , .		8
111	235&#x2013;275 GHz (x16) frequency multiplier chains with up to 0 dBm peak output power and low DC power consumption. , 2014, , .		36
112	All-Silicon Based Terahertz Integrated Components: The Next Generation of Terahertz Imaging Systems. , 2014, , .		0
113	A 240 GHz circular polarized FMCW radar based on a SiGe transceiver with a lens-integrated on-chip antenna. , 2014, , .		6
114	A 240 GHz circular polarized FMCW radar based on a SiGe transceiver with a lens-integrated on-chip antenna. , 2014, , .		5
115	A 0.53 THz Reconfigurable Source Module With Up to 1 mW Radiated Power for Diffuse Illumination in Terahertz Imaging Applications. IEEE Journal of Solid-State Circuits, 2014, 49, 2938-2950.	3.5	106
116	On design of differentially driven on-chip antennas with harmonic filtering for silicon integrated mm-wave and THz N-push oscillators. , 2014, , .		16
117	A 2&#x00D7;2 lens-integrated on-chip antenna system for a 820 GHz multiplier-chain source in SiGe technology. , 2014, , .		3
118	Wide bandwidth room-temperature THz imaging array based on antenna-coupled MOSFET bolometer. Sensors and Actuators A: Physical, 2014, 215, 96-104.	2.0	25
119	14.5 A 0.53THz reconfigurable source array with up to 1mW radiated power for terahertz imaging applications in 0.13&#x03BC;m SiGe BiCMOS. , 2014, , .		31
120	A Real-Time Terahertz Beam Monitoring Application with a 1024-pixel CMOS Terahertz Camera Module. , 2014, , .		1
121	A 288-GHz Lens-Integrated Balanced Triple-Push Source in a 65-nm CMOS Technology. IEEE Journal of Solid-State Circuits, 2013, 48, 1751-1761.	3.5	123
122	A 0.32 THz FMCW radar system based on low-cost lens-integrated SiGe HBT front-ends. , 2013, , .		32
123	Toward low-NEP room-temperature THz MOSFET direct detectors in CMOS technology. , 2013, , .		31
124	A 135&#x2013;170 GHz power amplifier in an advanced sige HBT technology. , 2013, , .		17
125	160-GHz Power Amplifier Design in Advanced SiGe HBT Technologies With $\{P\}_{m sat}$ in Excess of 10 dBm. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 939-947.	2.9	42
126	A Terahertz Detector Array in a SiGe HBT Technology. IEEE Journal of Solid-State Circuits, 2013, 48, 2002-2010.	3.5	61



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127	Methods for determining the exposure to THz radiation utilizing CMOS-based detectors. , 2013, , .		1
128	Lens-integrated on-chip antennas for THz direct detectors in SiGe HBT technology. , 2013, , .		13
129	Attempts for exposure assessment in the THz-frequency range using numerical computations. , 2012, , .		5
130	The ATLAS Level-1 Calorimeter Trigger: PreProcessor implementation and performance. Journal of Instrumentation, 2012, 7, P12008-P12008.	0.5	5
131	A 1 k-Pixel Video Camera for 0.7â€“1.1 Terahertz Imaging Applications in 65-nm CMOS. IEEE Journal of Solid-State Circuits, 2012, 47, 2999-3012.	3.5	399
132	On the co-design between on-chip antennas and THz MOSFET direct detectors in CMOS technology. , 2012, , .		9
133	A 288-GHz lens-integrated balanced triple-push source in a 65-nm CMOS technology. , 2012, , .		27
134	SiGe Circuits for THz Applications. , 2012, , .		2
135	Real-time video rate imaging with a 1k-pixel THz CMOS focal plane array. Proceedings of SPIE, 2012, , .	0.8	30
136	A 160-GHz Subharmonic Transmitter and Receiver Chipset in an SiGe HBT Technology. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 3286-3299.	2.9	65
137	Terahertz detector arrays in a high-performance SiGe HBT technology. , 2012, , .		6
138	Silicon CMOS/SiGe transceiver circuits for THz applications. , 2012, , .		11
139	A 1kpixel CMOS camera chip for 25fps real-time terahertz imaging applications. , 2012, , .		69
140	Subharmonic 220- and 320-GHz SiGe HBT Receiver Front-Ends. IEEE Transactions on Microwave Theory and Techniques, 2012, 60, 1397-1404.	2.9	118
141	A 220GHz subharmonic receiver front end in a SiGe HBT technology. , 2011, , .		6
142	Sub-millimeter wave active imaging with silicon integrated circuits. , 2011, , .		8
143	Lens-integrated THz imaging arrays in 65nm CMOS technologies. , 2011, , .		38
144	A broadband 0.6 to 1 THz CMOS imaging detector with an integrated lens. , 2011, , .		37

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145	A 820GHz SiGe chipset for terahertz active imaging applications. , 2011, , .		38
146	Active 220- and 325-GHz Frequency Multiplier Chains in an SiGe HBT Technology. IEEE Transactions on Microwave Theory and Techniques, 2011, 59, 1311-1318.	2.9	159
147	Fundamental mode colpitts VCOs at 115 and 165-GHz. , 2011, , .		14
148	Towards 3D-imaging with low-cost SiGe-Technology at 160GHz. , 2011, , .		2
149	A 160-GHz low-noise downconversion receiver front-end in a SiGe HBT technology. International Journal of Microwave and Wireless Technologies, 2011, 3, 347-353.	1.5	12
150	A SiGe quadrature transmitter and receiver chipset for emerging high-frequency applications at 160GHz. , 2010, , .		57
151	A 325 GHz frequency multiplier chain in a SiGe HBT technology. , 2010, , .		20
152	Terahertz heterodyne detection with silicon field-effect transistors. Applied Physics Letters, 2010, 96, .	1.5	98
153	Terahertz imaging with CMOS/BiCMOS process technologies. , 2010, , .		25
154	A 650GHz SiGe receiver front-end for terahertz imaging arrays. , 2010, , .		21
155	Terahertz imaging detectors in a 65-nm CMOS SOI technology. , 2010, , .		44
156	Efficient distributed self-mixing in silicon CMOS transistors. , 2009, , .		1
157	A CMOS focal-plane array for heterodyne terahertz imaging. , 2009, , .		24
158	A subharmonic front-end in SiGe:C technology for 94-GHz imaging arrays. International Journal of Microwave and Wireless Technologies, 2009, 1, 361-368.	1.5	0
159	Terahertz Imaging Detectors in CMOS Technology. Journal of Infrared, Millimeter, and Terahertz Waves, 2009, 30, 1269.	1.2	41
160	A 0.65 THz Focal-Plane Array in a Quarter-Micron CMOS Process Technology. IEEE Journal of Solid-State Circuits, 2009, 44, 1968-1976.	3.5	359
161	Terahertz heterodyne detection with silicon CMOS transistors. , 2009, , .		4
162	Rational design of high-responsivity detectors of terahertz radiation based on distributed self-mixing in silicon field-effect transistors. Journal of Applied Physics, 2009, 105, .	1.1	291

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163	Terahertz imaging with Si MOSFET focal-plane arrays. , 2009, , .		41
164	Schottky Barrier Diode Circuits in Silicon for Future Millimeter-Wave and Terahertz Applications. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 364-371.	2.9	72
165	A 94-GHz Monolithic Front-End for Imaging Arrays in SiGe:C Technology. , 2008, , .		7
166	A 600-GHz CMOS focal-plane array for terahertz imaging applications. , 2008, , .		64
167	A CMOS focal-plane array for terahertz imaging. , 2008, , .		14
168	A 94-GHz Monolithic Front-End for Imaging Arrays in SiGe:C Technology. , 2008, , .		10
169	The ATLAS Level-1 Calorimeter Trigger. Journal of Instrumentation, 2008, 3, P03001-P03001.	0.5	65
170	Silicon germanium based millimetre-wave ICs for Gbps wireless communications and radar systems. Semiconductor Science and Technology, 2007, 22, S236-S243.	1.0	20
171	Broadband planar millimeter wave dipole with flip-chip interconnect. , 2007, , .		2
172	A 20 dBm Fully-Integrated 60 GHz SiGe Power Amplifier With Automatic Level Control. IEEE Journal of Solid-State Circuits, 2007, 42, 1455-1463.	3.5	112
173	Silicon Schottky Diode Power Converters Beyond 100 GHz. , 2007, , .		16
174	Silicon Millimeter-Wave Radio Circuits at 60-100 GHz. , 2007, , .		23
175	High-efficiency 60 GHz antenna fabricated using low-cost silicon micromachining techniques. , 2007, , .		28
176	A 23-dBm 60-GHz Distributed Active Transformer in a Silicon Process Technology. IEEE Transactions on Microwave Theory and Techniques, 2007, 55, 857-865.	2.9	88
177	A 20dBm Fully-Integrated 60GHz SiGe Power Amplifier with Automatic Level Control. , 2006, , .		28
178	Wideband Cavity-backed Folded Dipole Superstrate Antenna for 60 GHz Applications. , 2006, , .		44
179	A 60GHz Class-E Power Amplifier in SiGe. , 2006, , .		27
180	A Silicon 60-GHz Receiver and Transmitter Chipset for Broadband Communications. IEEE Journal of Solid-State Circuits, 2006, 41, 2820-2831.	3.5	305

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181	Millimeter-wave design considerations for power amplifiers in an SiGe process technology. IEEE Transactions on Microwave Theory and Techniques, 2006, 54, 57-64.	2.9	19
182	Determination of the complex permittivity of packaging materials at millimeter-wave frequencies. IEEE Transactions on Microwave Theory and Techniques, 2006, 54, 1001-1010.	2.9	53
183	A chip-scale packaging technology for 60-GHz wireless chipsets. IEEE Transactions on Microwave Theory and Techniques, 2006, 54, 3387-3397.	2.9	146
184	Design and Compliance Testing of a SiGe WCDMA Receiver IC With Integrated Analog Baseband. Proceedings of the IEEE, 2005, 93, 1624-1636.	16.4	12
185	SiGe bipolar transceiver circuits operating at 60 GHz. IEEE Journal of Solid-State Circuits, 2005, 40, 156-167.	3.5	248
186	Pure-mode network analyzer concept for on-wafer measurements of differential circuits at millimeter-wave frequencies. IEEE Transactions on Microwave Theory and Techniques, 2005, 53, 934-937.	2.9	23
187	WCDMA direct-conversion receiver front-end comparison in RF-CMOS and SiGe BiCMOS. IEEE Transactions on Microwave Theory and Techniques, 2005, 53, 1181-1188.	2.9	21
188	Characterization of flip-chip interconnects up to millimeter-wave frequencies based on a nondestructive in situ approach. IEEE Transactions on Advanced Packaging, 2005, 28, 160-167.	1.7	17
189	A recursive un-termination method for nondestructive in situ S-parameter measurement of hermetically encapsulated packages. IEEE Transactions on Microwave Theory and Techniques, 2005, 53, 1845-1855.	2.9	3
190	Equivalent circuit model extraction of flip-chip ball interconnects based on direct probing techniques. IEEE Microwave and Wireless Components Letters, 2005, 15, 594-596.	2.0	18
191	The ATLAS level-1 calorimeter trigger architecture. IEEE Transactions on Nuclear Science, 2004, 51, 356-360.	1.2	18
192	Probe based MMW antenna measurement setup. , 2004, , .		72
193	A direct-conversion receiver IC for WCDMA mobile systems. IEEE Journal of Solid-State Circuits, 2003, 38, 1555-1560.	3.5	28
194	A direct-conversion receiver integrated circuit for WCDMA mobile systems. IBM Journal of Research and Development, 2003, 47, 337-353.	3.2	20
195	Statistical analysis and modelling of low-cost leadless packages for wireless applications based on non-destructive measurements. , 2003, , .		4
196	A novel simulation and verification approach in an ASIC design process. IEEE Transactions on Nuclear Science, 2002, 49, 307-311.	1.2	1
197	A mixed signal multi-chip module with high speed serial output links for the ATLAS level-1 trigger. IEEE Transactions on Nuclear Science, 2000, 47, 1463-1467.	1.2	0
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